

NTE62

Silicon NPN Transistor

High Voltage, Horizontal Deflection Output for TV

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	2500V
Collector–Emitter Voltage, V_{CEO}	900V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	3A
Peak	7A
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	50W
Operating Junction Temperature, T_j	+150°C
Storage Temperature Range, T_{stg}	–40° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1000\text{V}, I_E = 0$	–	–	50	μA
		$V_{CB} = 2500\text{V}, I_E = 0$	–	–	1.0	mA
	I_{CEO}	$V_{CE} = 900\text{V}, I_B = 0$	–	–	10	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$	–	–	1.0	mA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 1.5\text{A}$	3	–	15	–
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5\text{A}, I_B = 0.5\text{A}$	–	–	10	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1.5\text{A}, I_B = 0.5\text{A}$	–	–	1.25	V
Transition Frequency	f_t	$I_C = 1.5\text{A}$	–	–	1.0	μs

